

STARPOWER

SEMICONDUCTOR

IGBT

GD80TLQ120F1S

1200V/80A 3-level in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as solar power.

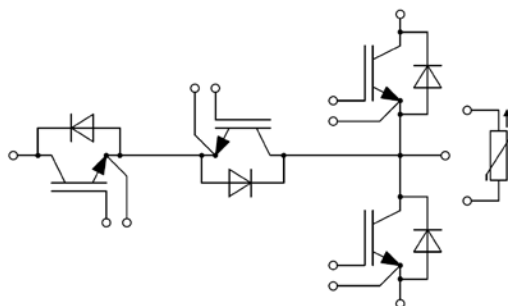
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- Low switching loss
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- Maximum junction temperature 175°C
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology

Typical Applications

- Solar power
- UPS
- 3-level-application

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**T1,T2 IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	110	A
	@ $T_C=90^{\circ}\text{C}$	80	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	160	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	450	W

D1,D2 Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	50	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	100	A

T3,T4 IGBT

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	93	A
	@ $T_C=65^{\circ}\text{C}$	75	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	150	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	231	W

D3,D4 Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	600	V
I_F	Diode Continuous Forward Current	60	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	120	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V

T1,T2 IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=80\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.95	2.40	V	
		$I_C=80\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.25			
		$I_C=80\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.30			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.2	6.0	6.8	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			TBD		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		TBD		nF	
C_{res}	Reverse Transfer Capacitance			TBD		nF	
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		TBD		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=350\text{V}, I_C=56\text{A}, R_G=4.0\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		68		ns	
t_r	Rise Time			11		ns	
$t_{d(off)}$	Turn-Off Delay Time			181		ns	
t_f	Fall Time			53		ns	
E_{on}	Turn-On Switching Loss			0.41		mJ	
E_{off}	Turn-Off Switching Loss			1.41		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=350\text{V}, I_C=56\text{A}, R_G=4.0\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		69		ns
t_r	Rise Time				14		ns
$t_{d(off)}$	Turn-Off Delay Time			226		ns	
t_f	Fall Time			65		ns	
E_{on}	Turn-On Switching Loss			0.72		mJ	
E_{off}	Turn-Off Switching Loss			1.95		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=350\text{V}, I_C=56\text{A}, R_G=4.0\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			70		ns
t_r	Rise Time				14		ns
$t_{d(off)}$	Turn-Off Delay Time			236		ns	
t_f	Fall Time			69		ns	
E_{on}	Turn-On Switching Loss			0.86		mJ	
E_{off}	Turn-Off Switching Loss			2.35		mJ	
I_{SC}	SC Data		$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=360\text{V}, V_{CEM} \leq 1200\text{V}$		375		A

D1,D2 Diode Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=50\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.75	2.20	V
		$I_F=50\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.65		
		$I_F=50\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.65		
Q_r	Recovered Charge	$V_R=350\text{V}, I_F=56\text{A},$ $-di/dt=5000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		5.2		μC
I_{RM}	Peak Reverse Recovery Current			105		A
E_{rec}	Reverse Recovery Energy			1.50		mJ
Q_r	Recovered Charge	$V_R=350\text{V}, I_F=56\text{A},$ $-di/dt=5000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		7.0		μC
I_{RM}	Peak Reverse Recovery Current			114		A
E_{rec}	Reverse Recovery Energy			2.10		mJ
Q_r	Recovered Charge	$V_R=350\text{V}, I_F=56\text{A},$ $-di/dt=5000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		8.1		μC
I_{RM}	Peak Reverse Recovery Current			118		A
E_{rec}	Reverse Recovery Energy			2.40		mJ

T3,T4 IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.45	1.90	V	
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.60			
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		1.70			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=1.2\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.1	5.8	6.4	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			/		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		4.62		nF	
C_{res}	Reverse Transfer Capacitance				0.14		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.80		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=350\text{V}, I_C=56\text{A}, R_G=4.0\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		84		ns	
t_r	Rise Time			10		ns	
$t_{d(off)}$	Turn-Off Delay Time			180		ns	
t_f	Fall Time			87		ns	
E_{on}	Turn-On Switching Loss				0.53		mJ
E_{off}	Turn-Off Switching Loss				1.86		mJ
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=350\text{V}, I_C=56\text{A}, R_G=4.0\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		85		ns
t_r	Rise Time				11		ns
$t_{d(off)}$	Turn-Off Delay Time			200		ns	
t_f	Fall Time			100		ns	
E_{on}	Turn-On Switching Loss				0.66		mJ
E_{off}	Turn-Off Switching Loss				2.20		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=350\text{V}, I_C=56\text{A}, R_G=4.0\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			86		ns
t_r	Rise Time				12		ns
$t_{d(off)}$	Turn-Off Delay Time			208		ns	
t_f	Fall Time			105		ns	
E_{on}	Turn-On Switching Loss				0.75		mJ
E_{off}	Turn-Off Switching Loss				2.50		mJ
I_{SC}	SC Data		$t_p \leq 6\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=350\text{V}, V_{CEM} \leq 600\text{V}$		380		A

D3,D4 Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=60\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.50	1.95	V
		$I_F=60\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.40		
		$I_F=60\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.40		
Q_r	Recovered Charge	$V_R=350\text{V}, I_F=56\text{A},$ $-di/dt=4000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		1.4		μC
I_{RM}	Peak Reverse Recovery Current			38		A
E_{rec}	Reverse Recovery Energy			0.20		mJ
Q_r	Recovered Charge	$V_R=350\text{V}, I_F=56\text{A},$ $-di/dt=4000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		2.7		μC
I_{RM}	Peak Reverse Recovery Current			45		A
E_{rec}	Reverse Recovery Energy			0.50		mJ
Q_r	Recovered Charge	$V_R=350\text{V}, I_F=56\text{A},$ $-di/dt=4000\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		3.1		μC
I_{RM}	Peak Reverse Recovery Current			50		A
E_{rec}	Reverse Recovery Energy			0.60		mJ

NTC Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			22.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_C=100^\circ\text{C}, R_{100}=1486.1\Omega$	-5		5	%
P_{25}	Power Dissipation				200	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		4000		K

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per T1,T2 IGBT)		0.303	0.333	K/W
	Junction-to-Case (per D1,D2 Diode)		0.764	0.840	
	Junction-to-Case (per T3,T4 IGBT)		0.590	0.649	
	Junction-to-Case (per D3,D4 Diode)		0.860	0.946	
R_{thCH}	Case-to-Heatsink (per T1,T2 IGBT)		0.158		K/W
	Case-to-Heatsink (per D1,D2 Diode)		0.399		
	Case-to-Heatsink (per T3,T4 IGBT)		0.309		
	Case-to-Heatsink (per D3,D4 Diode)		0.450		
	Case-to-Heatsink (per Module)		0.035		
M	Mounting Torque, Screw M4	2.0		2.2	N.m
G	Weight of Module		26		g

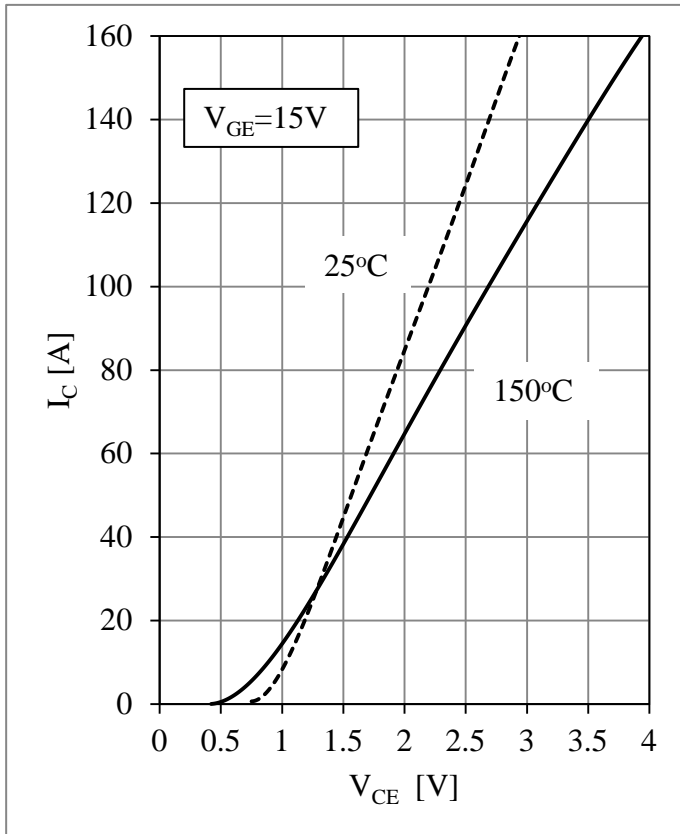


Fig 1. T1,T2 IGBT Output Characteristics

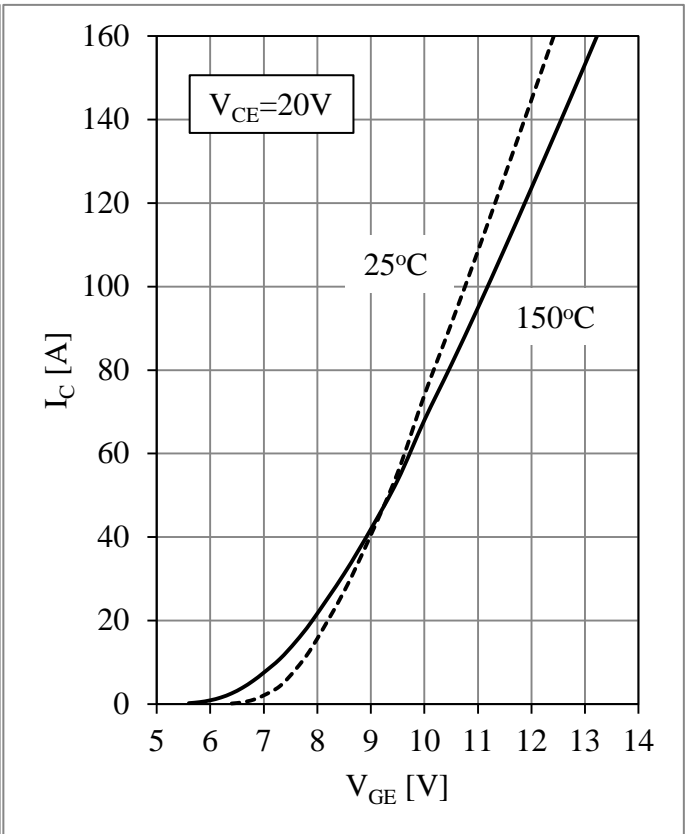


Fig 2. T1,T2 IGBT Transfer Characteristics

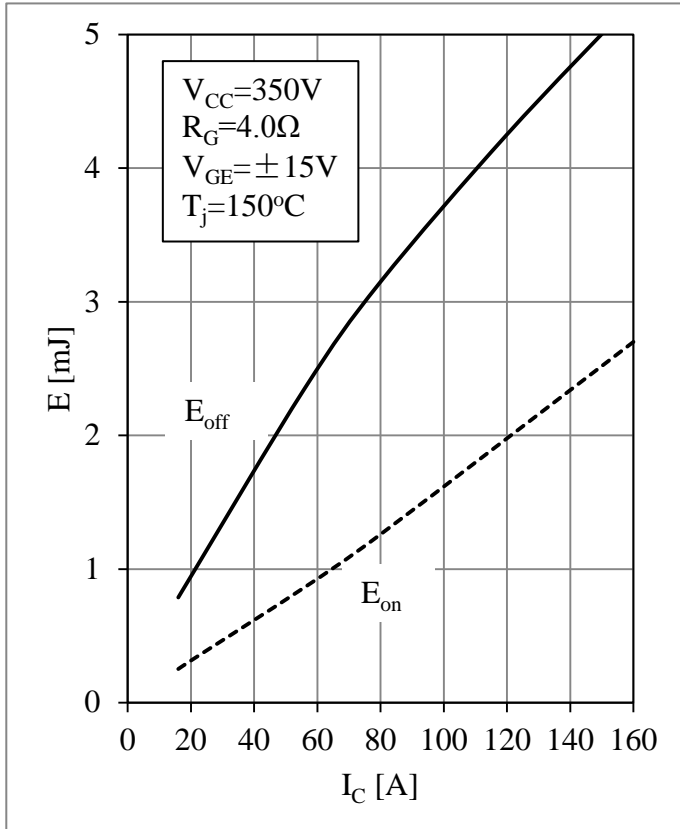


Fig 3. T1,T2 IGBT Switching Loss vs. I_C

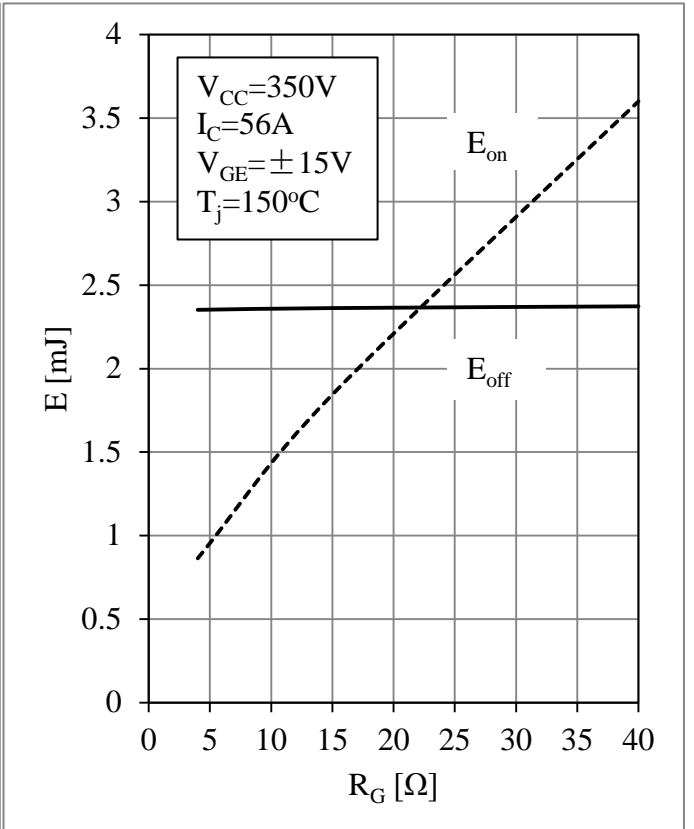


Fig 4. T1,T2 IGBT Switching Loss vs. R_G

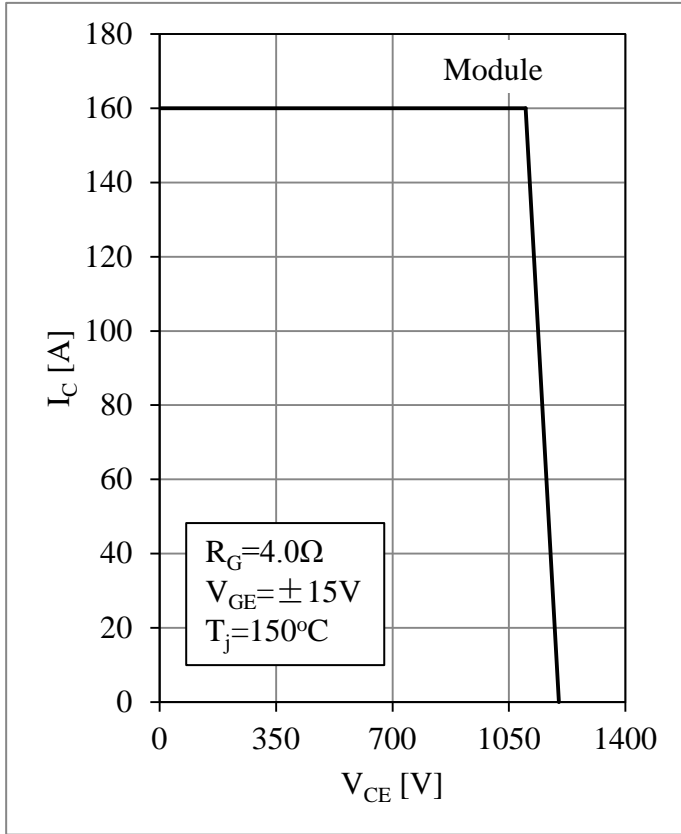


Fig 5. T1,T2 RBSOA

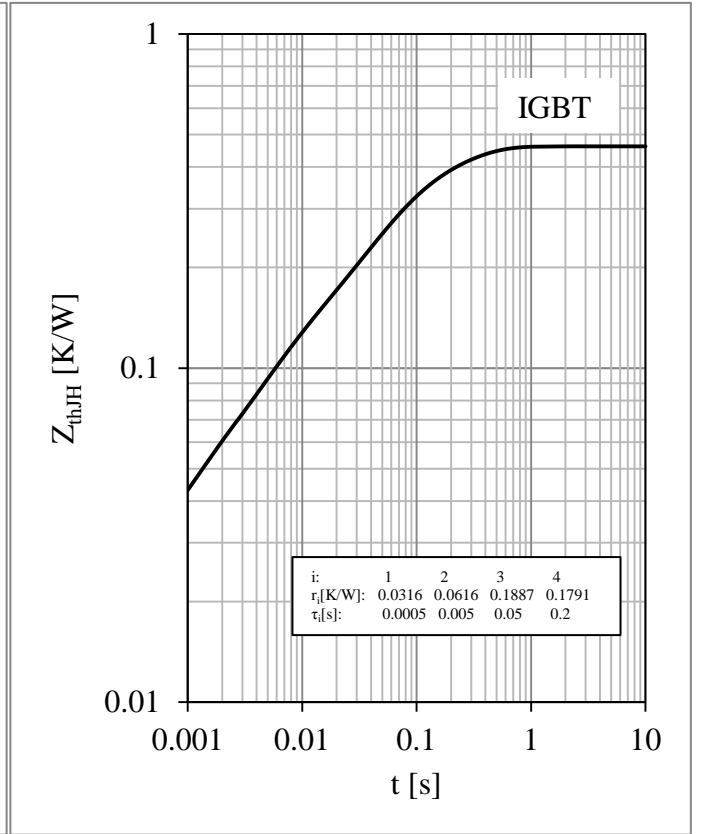


Fig 6. T1,T2 IGBT Transient Thermal Impedance

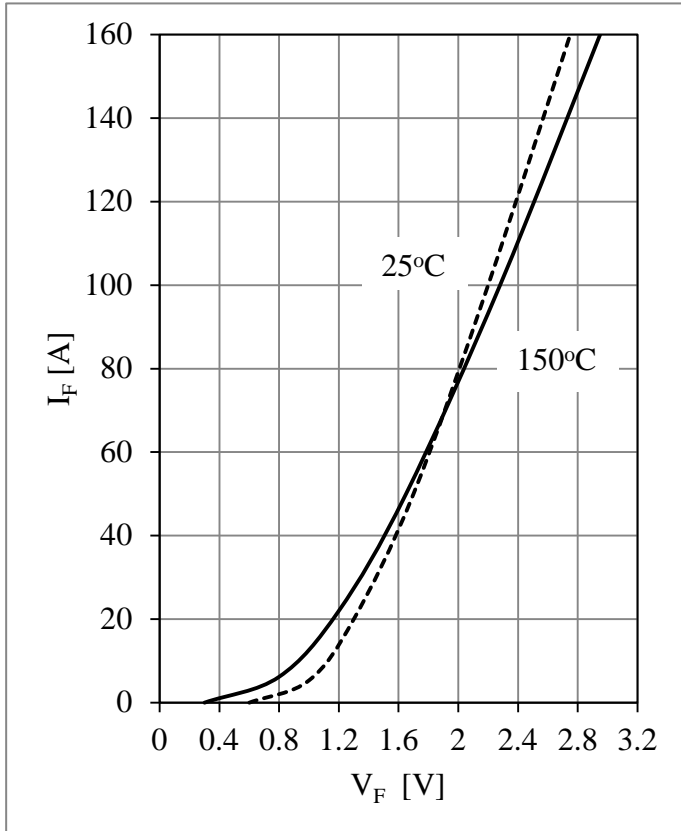


Fig 7. D1,D2 Diode Forward Characteristics

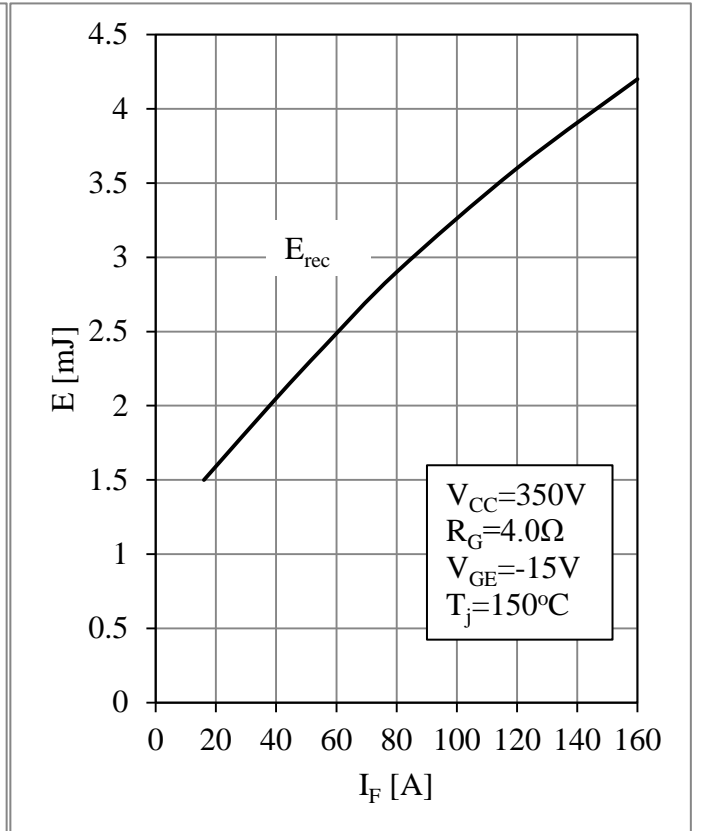


Fig 8. D1,D2 Diode Switching Loss vs. I_F

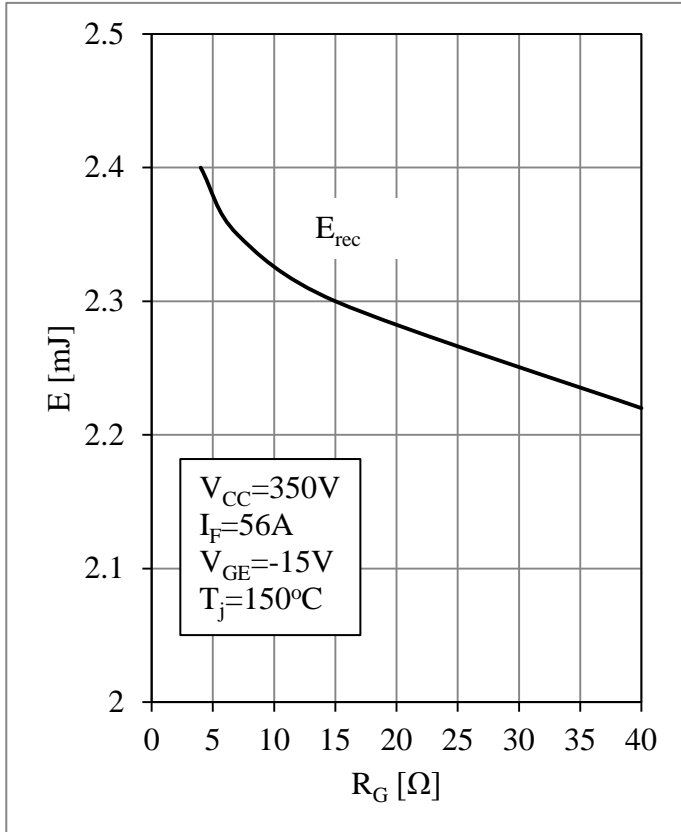


Fig 9. D1,D2 Diode Switching Loss vs. R_G

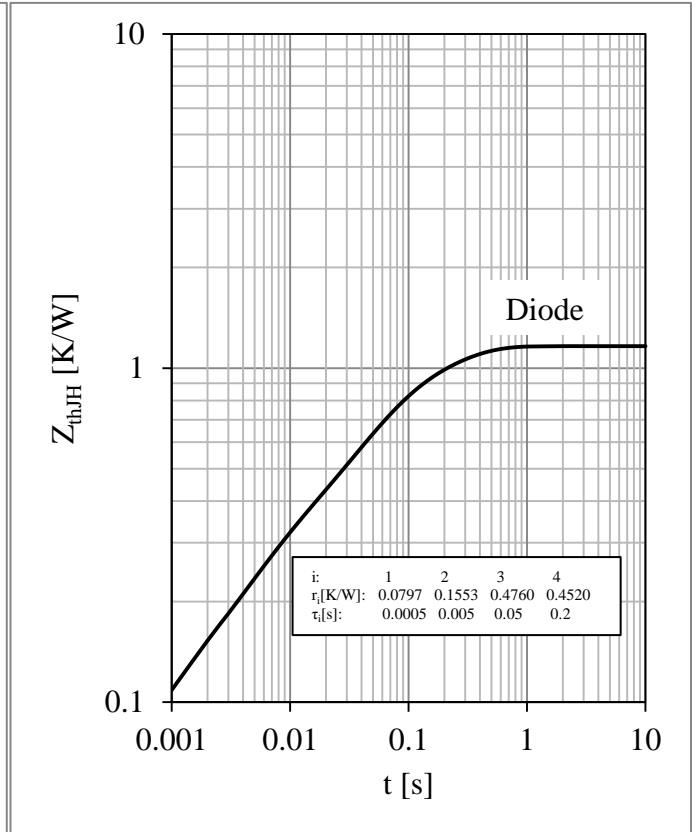


Fig 10. D1,D2 Diode Transient Thermal Impedance

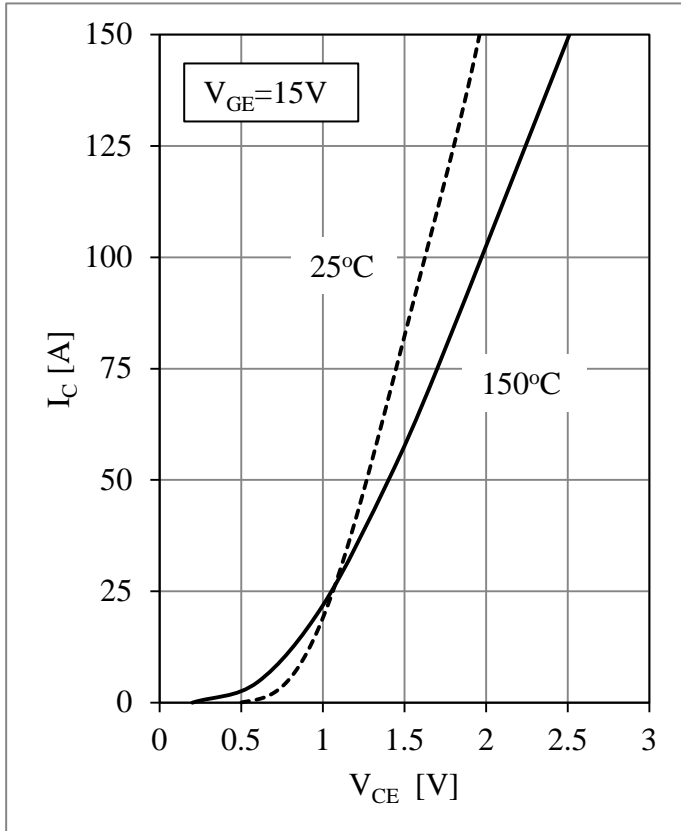


Fig 11. T3,T4 IGBT Output Characteristics

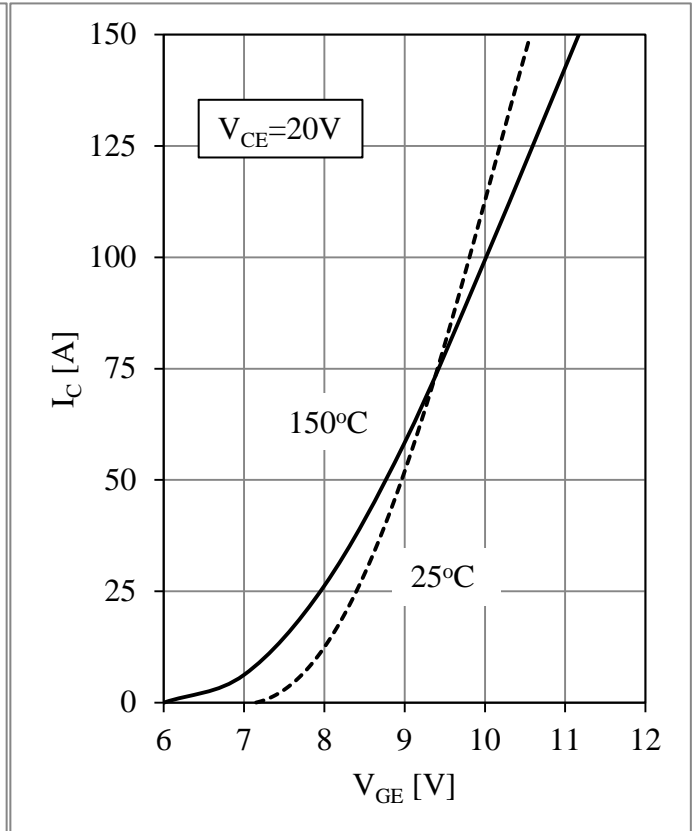


Fig 12. T3,T4 IGBT Transfer Characteristics

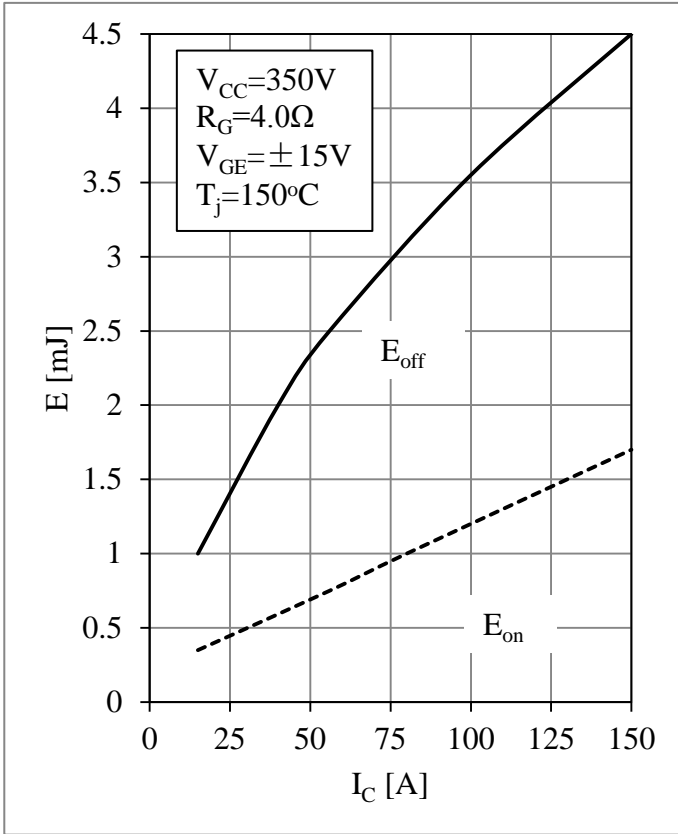


Fig 13. T3,T4 IGBT Switching Loss vs. I_C

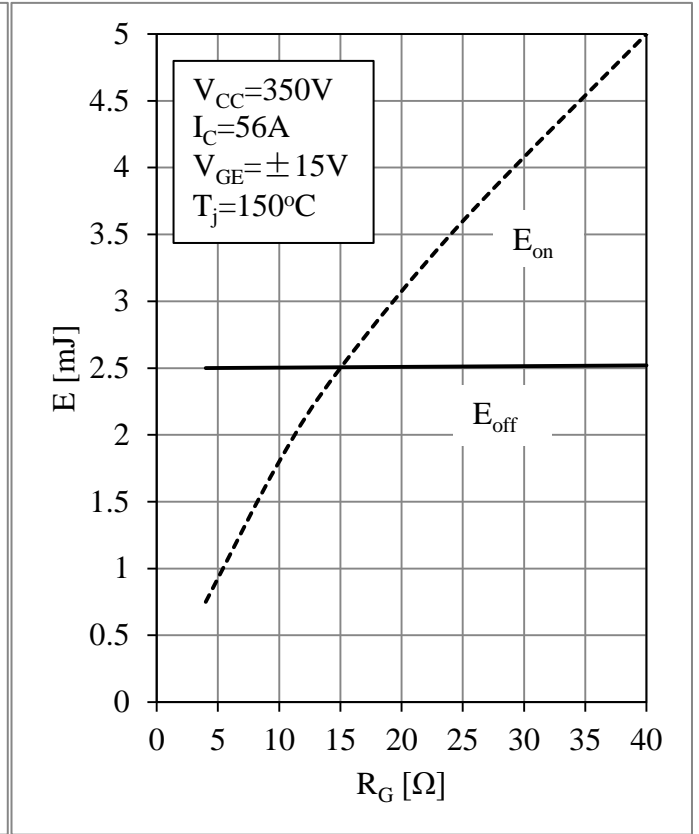


Fig 14. T3,T4 IGBT Switching Loss vs. R_G

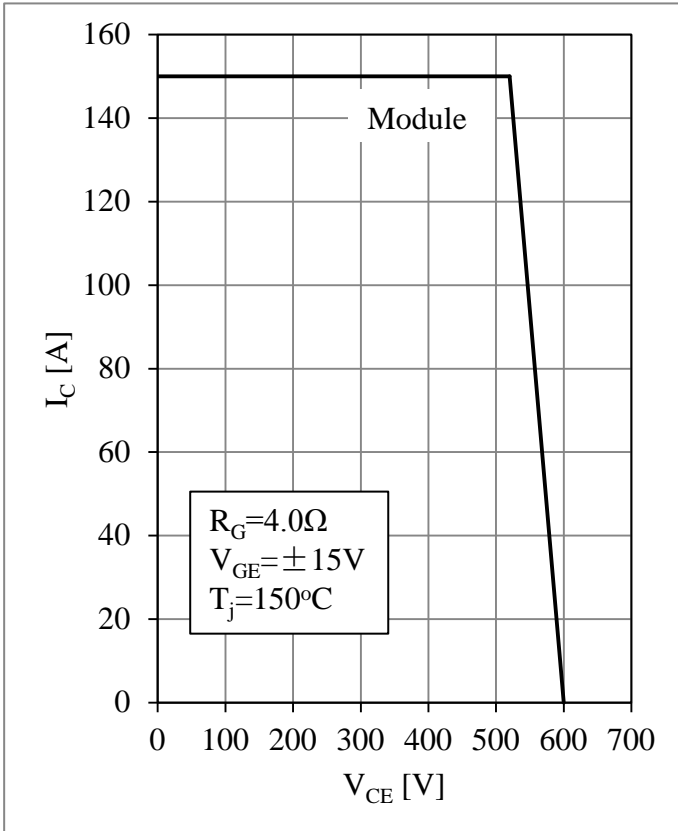


Fig 15. T3,T4 RBSOA

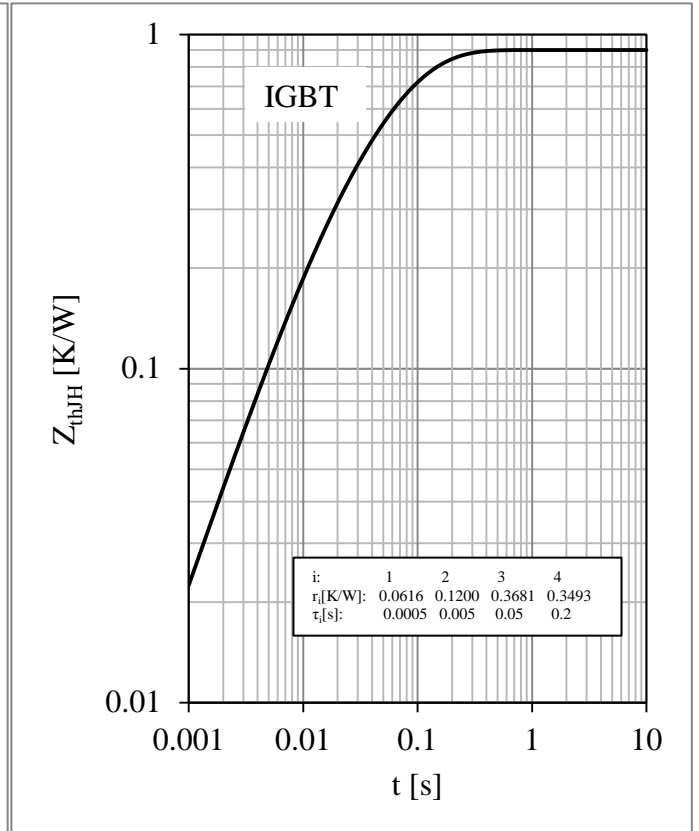


Fig 16. T3,T4 IGBT Transient Thermal Impedance

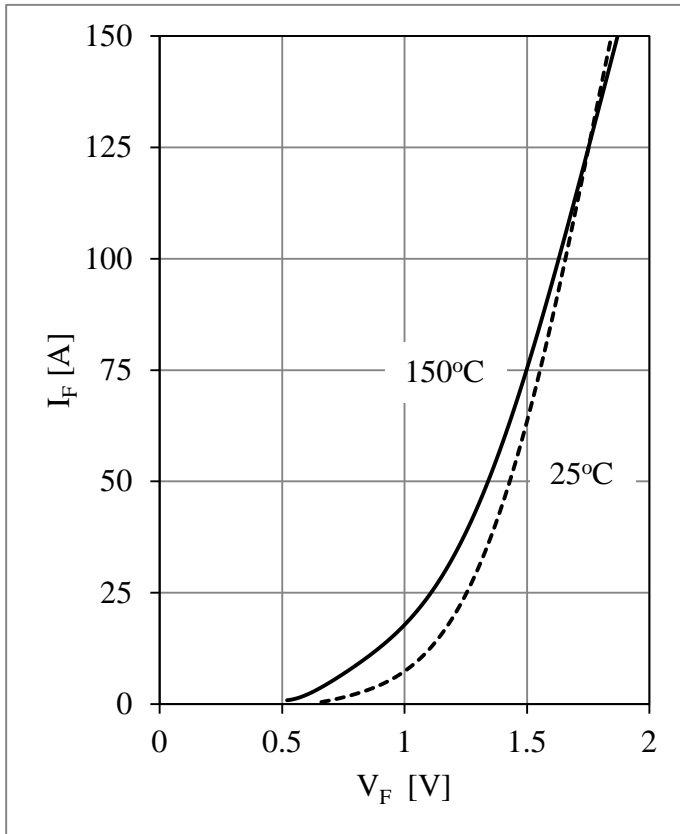


Fig 17. D3,D4 Diode Forward Characteristics

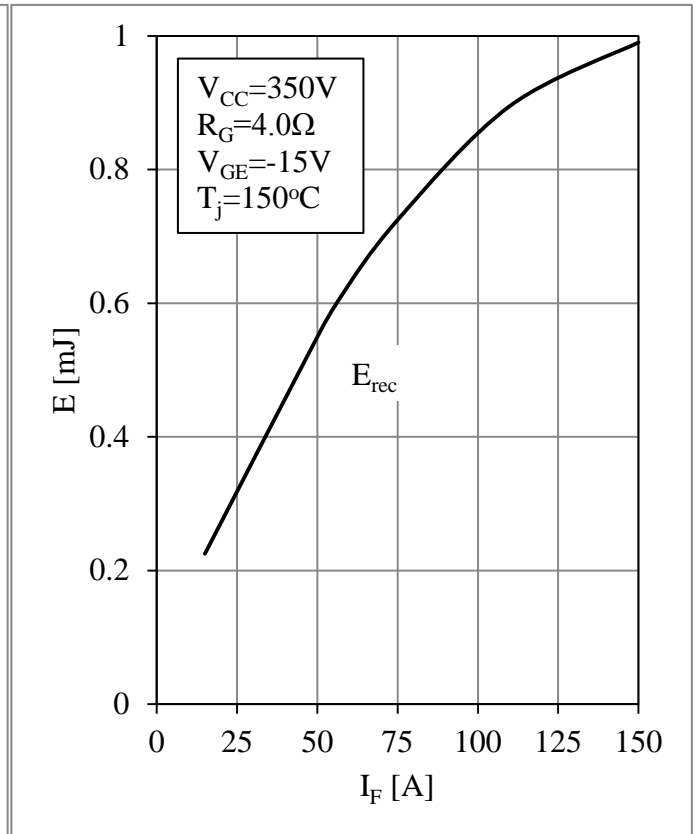


Fig 18. D3,D4 Diode Switching Loss vs. I_F

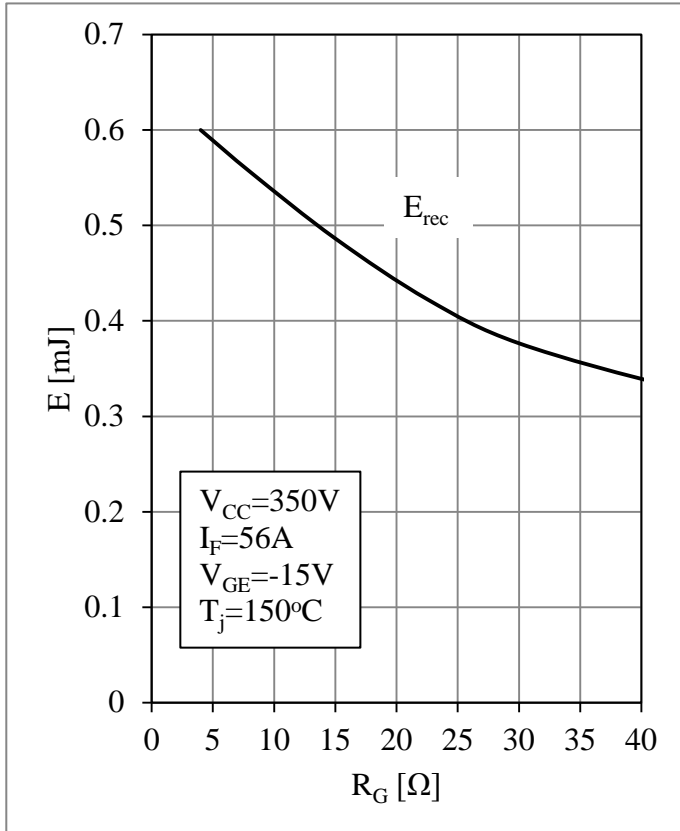


Fig 19. D3,D4 Diode Switching Loss vs. R_G

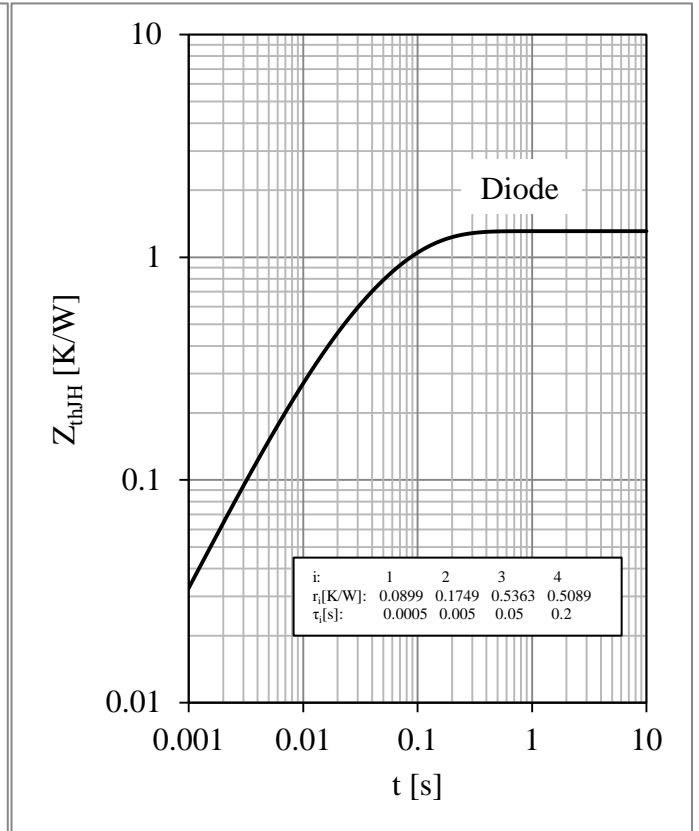


Fig 20. D3,D4 Diode Transient Thermal Impedance

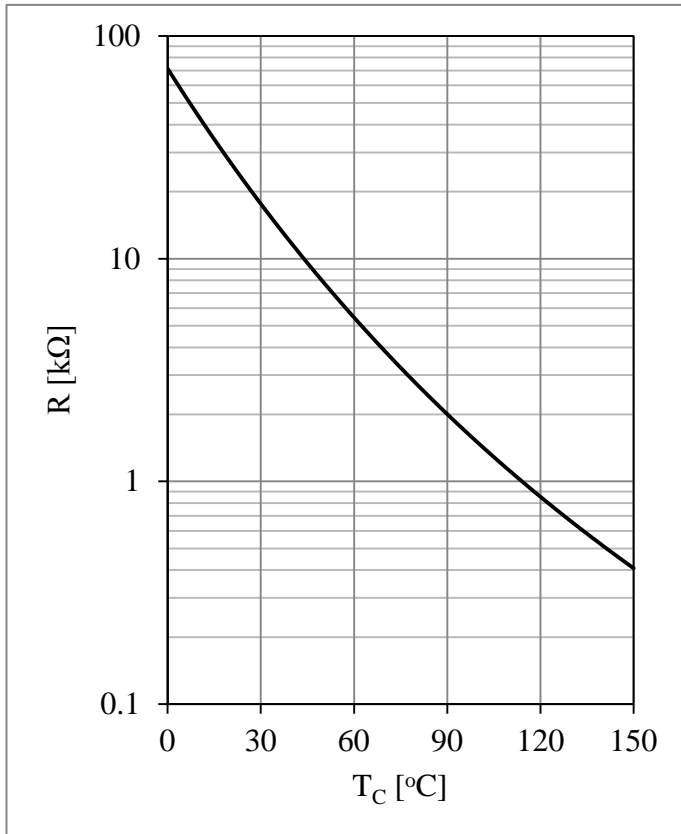
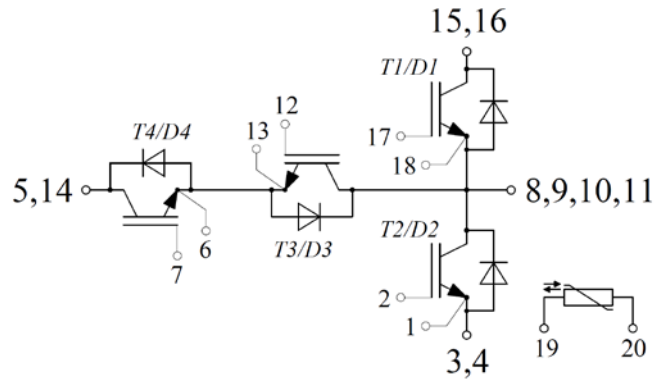


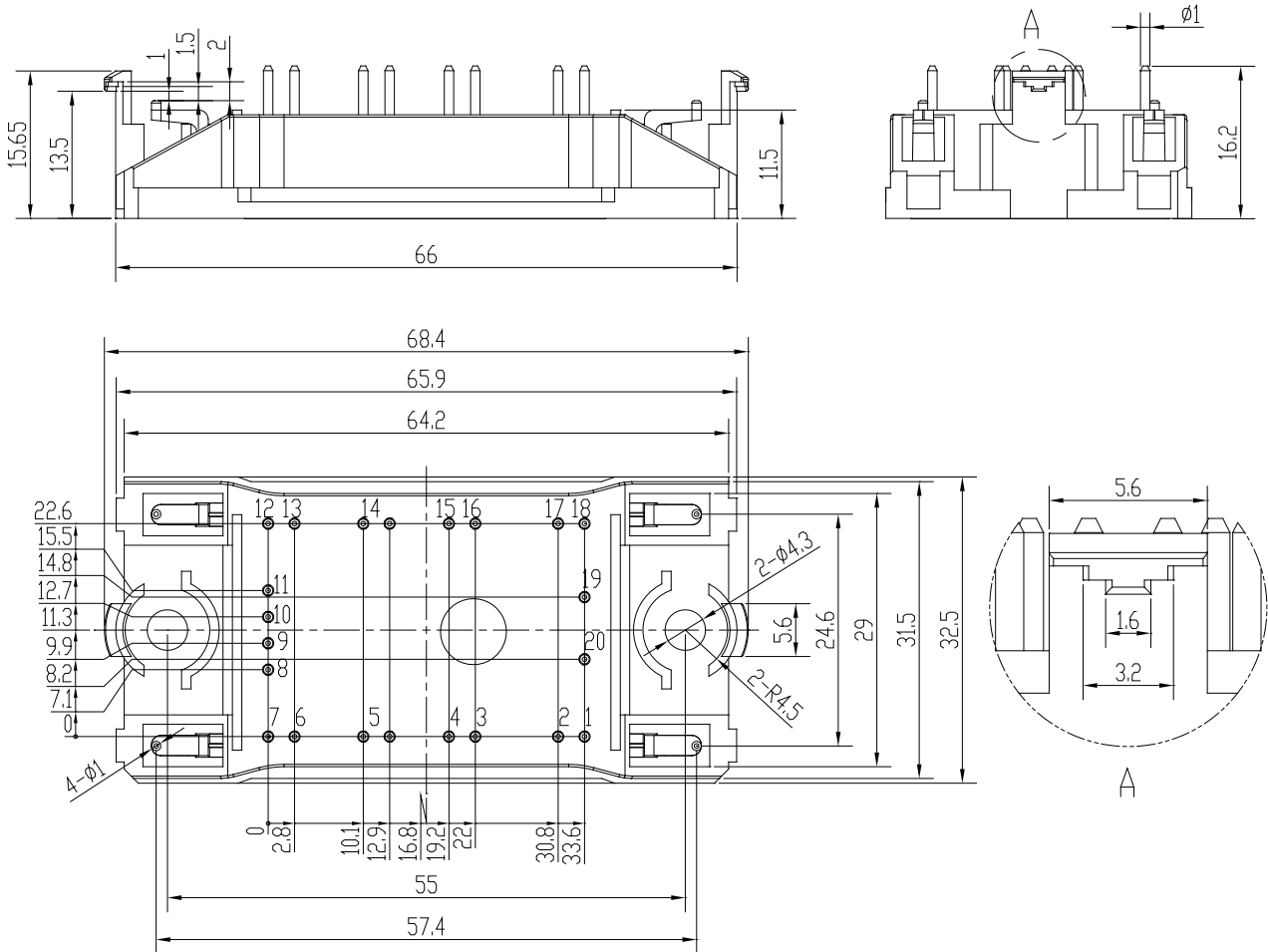
Fig 21. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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